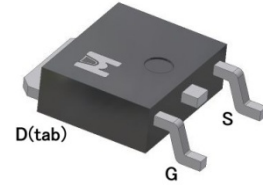


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV _{DSS}	250V
R _{DS(on)} (MAX.)	1 Ω
I _D	4.4A



UIS, R_g 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _C = 25 °C	I _D	4.4	A
	T _C = 100 °C		2.6	
Pulsed Drain Current ¹		I _{DM}	17.6	
Avalanche Current		I _{AS}	1	
Avalanche Energy	L = 3mH, I _D =1A, R _G =25Ω	E _{AS}	1.5	mJ
Repetitive Avalanche Energy ²	L = 1mH	E _{AR}	0.5	
Power Dissipation	T _C = 25 °C	P _D	29	W
	T _C = 100 °C		11	
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	R _{θJC}		4.2	°C / W
Junction-to-Ambient	R _{θJA}		62.5	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%



ELECTRICAL CHARACTERISTICS ($T_c = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 10mA$	250			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	2	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200V, V_{GS} = 0V$			1	μA
		$V_{DS} = 200V, V_{GS} = 0V, T_J = 125\text{ }^\circ\text{C}$			25	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	4.4			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 2.2A$		0.82	1.0	Ω
		$V_{GS} = 5V, I_D = 1.1A$		0.90	1.1	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 50V, I_D = 2.2A$		2.3		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		1224		pF
Output Capacitance	C_{oss}			27		
Reverse Transfer Capacitance	C_{rss}			23		
Gate Resistance	R_g	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		2.0		Ω
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = 200V, V_{GS} = 10V,$ $I_D = 2.2A$		32		nC
Gate-Source Charge ^{1,2}	Q_{gs}			4		
Gate-Drain Charge ^{1,2}	Q_{gd}			8.1		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = 125V,$ $I_D = 1A, V_{GS} = 10V, R_G = 6\Omega$		10		nS
Rise Time ^{1,2}	t_r			65		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			20		
Fall Time ^{1,2}	t_f			35		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_c = 25\text{ }^\circ\text{C}$)						
Continuous Current	I_S				4.4	A
Pulsed Current ³	I_{SM}				17.6	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F = 4.4A, di_F/dt = 100A / \mu S$		125		nS
Reverse Recovery Charge	Q_{rr}			500		nC

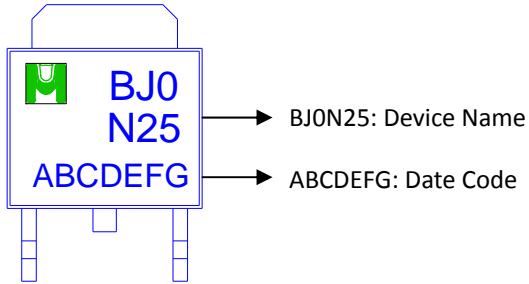
¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

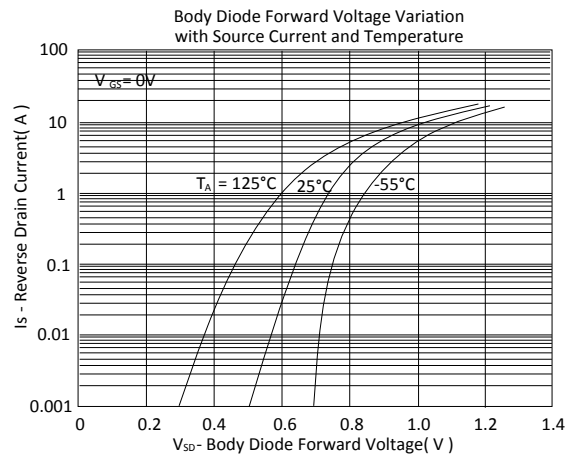
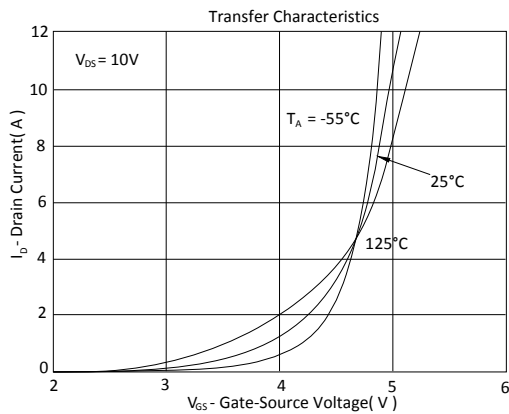
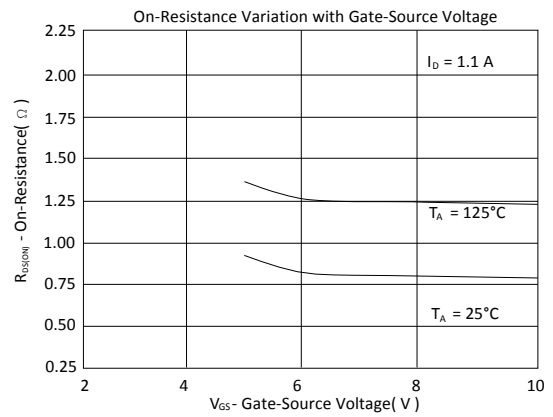
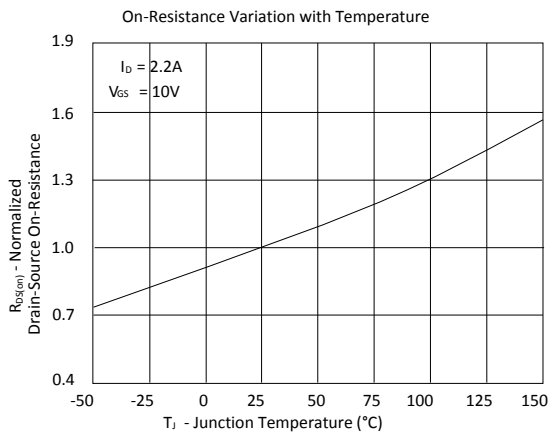
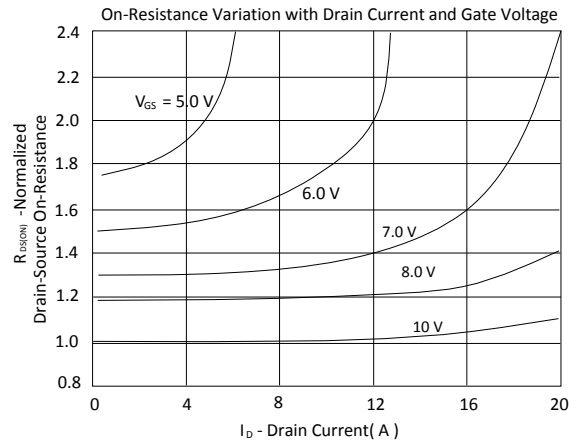
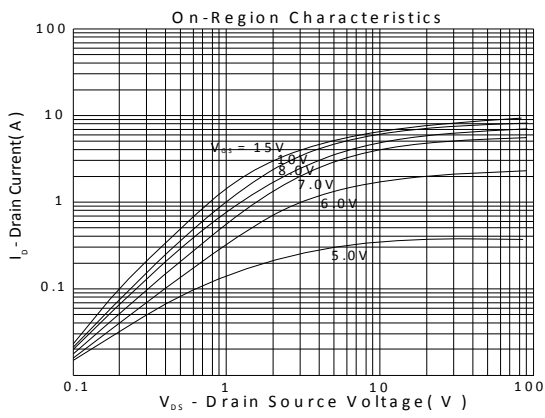
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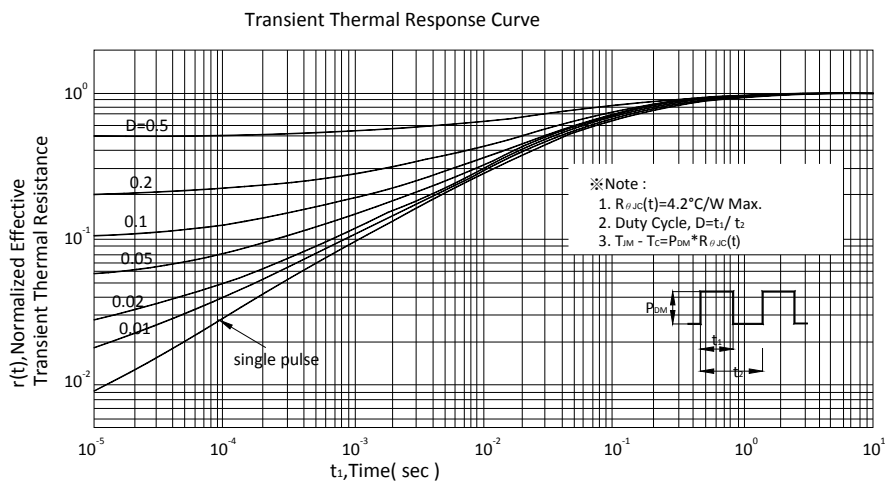
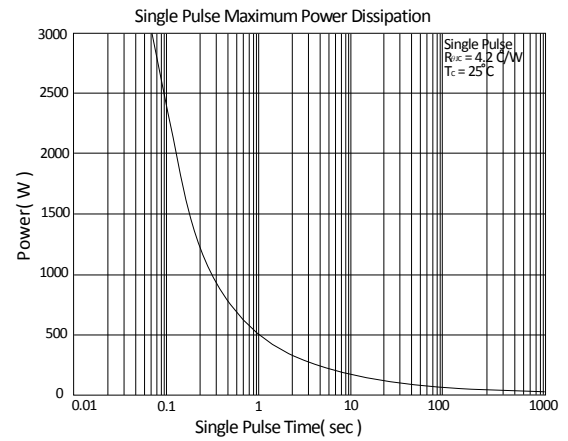
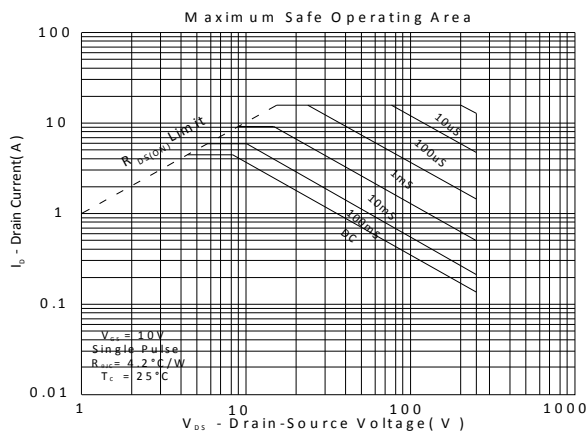
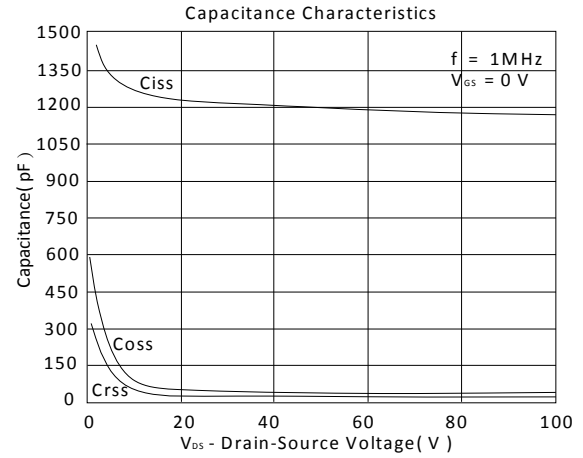
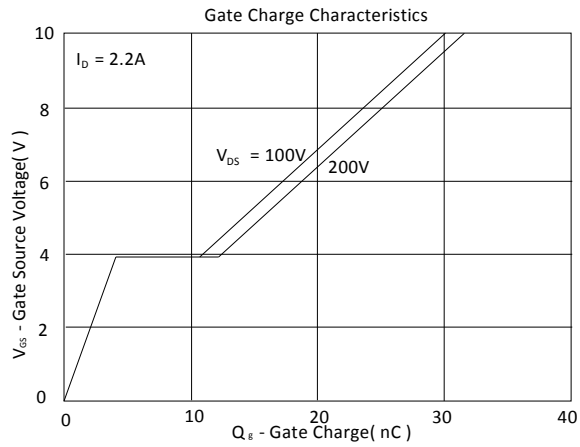
Device Name: EMBJ0N25A for DPAK (TO-252)





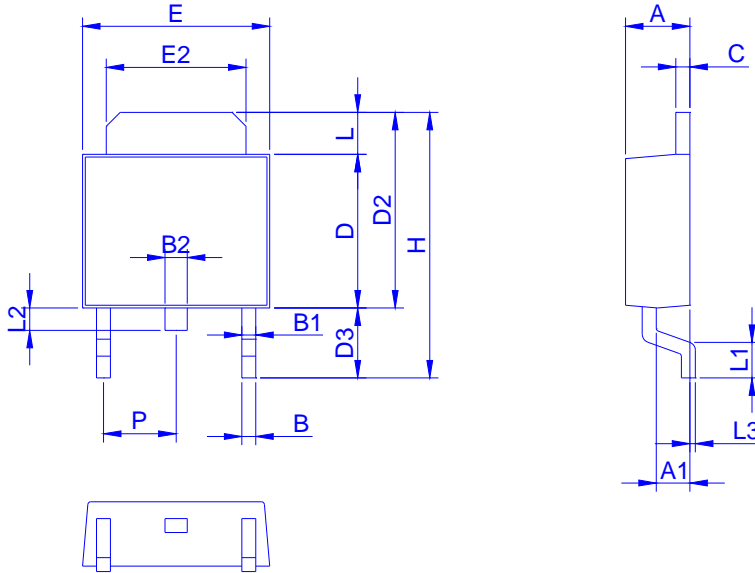
TYPICAL CHARACTERISTICS







Outline Drawing



Dimension in mm

Dimension	A	A1	B	B1	B2	C	D	D2	D3	E	E2	H	L	L1	L2	L3	P
Min.	2.10	0.95	0.30	0.40	0.60	0.40	5.30	6.70	2.20	6.40	4.80	9.20	0.89	0.90	0.50	0.00	2.10
Max.	2.50	1.30	0.85	0.94	1.00	0.60	6.20	7.30	3.00	6.70	5.45	10.15	1.70	1.65	1.10	0.30	2.50

Footprint

